


EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2030	703/2.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/14 14:30
L2	260	L1 and (impur\$4 pileup defects diffusion)	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/14 14:39
L3	82	716/19-21 and (impur\$4 pileup defects diffusion)	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/14 14:39
L4	724	(716/19-21).ccls. and (impur\$4 pileup defects diffusion)	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/14 14:39
L5	79	(716/19-21).ccls. and (impur\$4 pileup)	US-PGPUB; USPAT; USOCR	OR	OFF	2006/11/14 14:39
L7	341	716/20.ccls.	US-PGPUB; USPAT	OR	OFF	2006/11/14 14:58
L8	1	716/20.ccls. and (impur\$4 adj pileup)	US-PGPUB; USPAT	OR	OFF	2006/11/14 14:59
L9	7	(model\$4 with semiconductor with (device process) with impurity).clm.	US-PGPUB; USPAT	OR	OFF	2006/11/14 15:03
L10	3	(model\$4 with semiconductor with impurity with distance).clm.	US-PGPUB; USPAT	OR	OFF	2006/11/14 15:08
L11	0	(model\$4 with semiconductor with impurity with lambda).clm.	US-PGPUB; USPAT	OR	OFF	2006/11/14 15:03
L12	1	"6594625".pn.	US-PGPUB; USPAT	OR	OFF	2006/11/14 15:06
L13	0	(model\$4 with semiconductor with impurity with (gate source drain)).clm.	US-PGPUB; USPAT	OR	OFF	2006/11/14 15:08
L14	4	(US-20010025367-\$).did. or (US-5933359-\$ or US-5737250-\$ or US-5502643-\$).did.	US-PGPUB; USPAT	OR	OFF	2006/11/14 15:15
L15	0	(fair with diffusion with model\$4).clm.	US-PGPUB; USPAT	OR	OFF	2006/11/14 15:30
L16	15	(fair with diffusion with model\$4)	US-PGPUB; USPAT	OR	OFF	2006/11/14 15:30

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Date: 11/14/2006
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 PALM INTRANET

Inventor Name Search Result

Your Search was:

Last Name = HAYASHI

First Name = HIROKAZU

Application#	Patent#	Status	Date Filed	Title	Inventor Name
92293005	Not Issued	166	01/03/1989	CATIONIC ELECTRODEPOSITION COATING COMPOSITION	HAYASHI, HIROKAZU
92318720	4904361	150	03/03/1989	ELECTRODEPOSITION COATING COMPOSITION	HAYASHI, HIROKAZU
92701632	5089101	150	05/15/1991	CATIONIC ELECTRODEPOSITION COATING COMPOSITION	HAYASHI, HIROKAZU
98140552	5452019	150	10/25/1993	PROJECTED IMAGE DISPLAYING APPARATUS AND A METHOD OF CORRECTING COLOR UNEVENNESS THEREIN	HAYASHI, HIROKAZU
99245860	6581028	150	02/08/1999	PROFILE EXTRACTION METHOD AND PROFILE EXTRACTION APPARATUS	HAYASHI, HIROKAZU
99519856	6277684	150	03/06/2000	A METHOD OF FABRICATING A SOI STRUCTURE SEMICONDUCTOR DEVICE	HAYASHI, HIROKAZU
92313421	6594635	150	02/13/2001	METHOD FOR MODELING DIFFUSION OF IMPURITIES IN A SEMICONDUCTOR	HAYASHI, HIROKAZU
92891400	6566712	150	06/27/2001	SOI STRUCTURE SEMICONDUCTOR DEVICE AND A FABRICATION METHOD THEREOF	HAYASHI, HIROKAZU
10059176	Not Issued	80	01/12/2002	Method for modeling semiconductor device process	HAYASHI, HIROKAZU
10668261	6981236	150	09/24/2003	METHOD FOR MODELING SEMICONDUCTOR DEVICE AND NETWORK	HAYASHI, HIROKAZU
10780928	7000201	150	02/19/2004	EVALUATION TEG FOR SEMICONDUCTOR DEVICE AND METHOD OF EVALUATION	HAYASHI, HIROKAZU
10933271	Not Issued	41	09/03/2004	ESD protection device modeling method and ESD simulation method	HAYASHI, HIROKAZU
10989011	Not Issued	83	11/16/2004	Semiconductor device and method of manufacturing the same	HAYASHI, HIROKAZU
11092338	Not Issued	30	12/03/2004	Method of evaluating semiconductor device	HAYASHI, HIROKAZU
11180681	Not Issued	30	07/14/2005	Semiconductor device and method of producing the same	HAYASHI, HIROKAZU
11276823	Not Issued	30	03/15/2006	ELECTRO-STATIC DISCHARGE PROTECTION CIRCUIT AND SEMICONDUCTOR DEVICE HAVING THE SAME	HAYASHI, HIROKAZU
11284138	Not Issued	20	11/22/2005	Design and simulation methods for electrostatic protection circuits	HAYASHI, HIROKAZU
11449007	Not Issued	20	06/08/2006	Evaluation TEG for semiconductor device and method of evaluation	HAYASHI, HIROKAZU
11516752	Not Issued	25	09/07/2006	Load driving device	HAYASHI, HIROKAZU
11578202	Not Issued	19	01/01/0001	Pile fabric and method for producing the same	HAYASHI, HIROKAZU

Inventor Search Completed: No Records to Display.

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C. Gardiner

A. Juncal

O. Gummesson

D.Klaassen - Solid-State Electronics: An International Journal, 1992 - csa.com

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Numerical simulation of a steady-state electron shock wave in a submicrometer semiconductor device - group of 2 »

C. Gardiner - Electron Devices, IEEE Transactions on, 1991

... state electron devices will ... of electron-phonon and electron-impurity collisions ... in 1D, the hydrodynamic model consists of ... Cited by 58 - Related Articles - Web Search

Rigorous thermodynamic treatment of heat generation and conduction in semiconductor device modeling - group of 2 »

G.K. Wachutka - Computer-Aided Design of Integrated Circuits and Systems, ..., 1990 - aeesexplore.ieee.org

... heating on the performance of a semiconductor device proves to ... Thus the extended model also applies to direct semi ... of donors and acceptors (impurity freeze-out ... Cited by 60 - Related Articles - Web Search

poisson Quasi-Hydrodynamic Semiconductor Equations

A. Jungel - 2001 - books.google.com

... mathematical modeling and simulation of charge transport in semiconductors have become a thriving research area in applied mathematics. Semiconductor device ... Cited by 73 - Related Articles - Web Search - BL Direct

Simulation of negative-effective-mass terahertz oscillators - group of 2 »

J.C. Cao, H.C. Liu, X.L. Lei - Journal of Applied Physics, 2006 - link.aip.org

... balance-equation theory and a time-dependent drift-diffusion model ... we consider the scatterings by hole-impurity, hole-acoustic phonon ... Semiconductor devices ... Cited by 20 - Related Articles - Web Search - BL Direct

Simulation of terahertz generation at semiconductor surfaces - group of 5 »

M.B. Johnston, D.M. Whitaker, A. Corchia, A.G. Davies, ..., Physical Review B, 2002 - APS

... emission is particularly important when modeling hot carriers ... and is the mass density of the semiconductor ... Impurity scattering is an important mechanism for ... Cited by 34 - Related Articles - Web Search - BL Direct

Quantitative two-dimensional dopant profile measurement and inverse modeling by scanning capacitance ... - group of 3 »

Y. Huang, C.C. Williams, J. Slinkman - Applied Physics Letters, 2008 - link.aip.org

... a nanometer scale up at a semiconductor surface, and ... A quasi-1D model is used to extract dopant ... Doping and impurity implantation in germanium and silicon ... Cited by 23 - Related Articles - Web Search - BL Direct

Quantification of scanning capacitance microscopy imaging of the - group of 3 »

M.L. O'Malley, G.L. Timp, S.V. Mostolo, J.P. Gamio, R.N. ... - Applied Physics Letters, 2006 - link.aip.org

... Semiconductor devices. Semiconductor-device characterization, design, and modeling ... Impurity concentration, distribution, and gradients. Impurity concentration, distribution, and gradients. Cited by 28 - Related Articles - Web Search - BL Direct

poisson Modeling and Simulation of Wide Bandgap Semiconductor Devices: 4H-SiC - group of 2 »

M. Ludes - 2002 - deposit.dtb.de

... extensions compared to conventional semiconductor transport models ... mechanism, a generic model describing ... material properties, and general impurity kinetics of ... Cited by 7 - Related Articles - Web Search - Library Search





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D.Berlman
J.Hopfield

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A 3-dimensional process-simulator based on an open architecture

T. Wada, H. Umemoto, M. Fujimaga, M. Kimura, T. Uchida, ... - Simulation of Semiconductor Processes and Devices, 1999 ... , 1999 - IEEE Press
... expected to predict semiconductor device performance, especially process-simulator model (I, point defect model[2] for impurity diffusion, visco ...

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Impurity-point defects complexes. Diffusion studies in Si and SiGe, and electrical studies in Ga - group of 3

J. Page-Pederson - phys.aust.
... ment in year 2008, as assessed in the Semiconductor Industry Association Roadmap
... Is easily seen that a very precise simulation of impurity redistribution at ...
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Calculation of tunneling matrix elements in solid systems: mixed-valence dithiaspirocyclobutane ... - group of 2

D.N. Berlman, J.J. Hopfield - Journal of the American Chemical Society, 1984 - pubs.acs.org
... or on neighboring impurities. Faulkner and Hopfield developed a theory of the optical properties for a class of these doped semiconductor ... These problems ...
Cited by 19 - Related Articles - Web Search

SYMPOSIUM.E - group of 4

S. Stemmer, C.R. Abernathy, E. Gusev, D.G. Schlom - Scanning - mrs.org
... particular mode, whether it is due to a phonon, an impurity, or a ... Physics, University of Tsukuba, Tsukuba, Ibaraki 305-8573, Japan; Semiconductor Leading Edge ...
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RB Fair, JCC Tsai, Journal of the Electrochemical Society, 2008 - link.aip.org
... RB Fair, JCC Tsai, ... In this model it is shown that three intrinsic P diffusion coefficients exist, each ... Doping and Impurity Implantation in germanium and silicon.
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Model for the current-voltage characteristics of ultrathin oxide after soft breakdown - group of 3
M Houssa, T Nuyt, P Mertens, MM Heyns, Journal of Applied Physics, 2008 - link.aip.org
... prediction of the model is in fair agreement with ... Metal-Insulator-Semiconductor structures (including semiconductor-to-insulator ... Impurity and defect levels ...
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Point Defect Charge-State Effects on Transient Diffusion of Dopants in Si - group of 2

RB Fair, Journal of the Electrochemical Society, 2008 - link.aip.org
... 1990). Richard B. Fair. Abstract. ... Constant. Keywords: Semiconductor materials
... theory. ... Doping and Impurities in Solids.
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Boron Diffusion in Silicon-Concentration and Orientation Dependence, Background Effects, and Profile... - group of 2

RB Fair, Journal of the Electrochemical Society, 2008 - link.aip.org
... Richard B. Fair, ... and retarded accelerated diffusion in the presence of n-type impurities. This paper discusses a model of B diffusion which can be used to ...
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"Spin"-dip scattering of holes in semiconductor quantum wells - group of 4

R Ferreira, G Bastard, Physical Review B, 1991 - APS
... flip relaxation time of holes in semiconductor quantum wells ... the three-level model gives a fair account of ... plane wave vector of the impurity-assisted "spin" ...
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Interface-band-polarity model for semiconductor heterojunction band offsets - group of 4

WJ Li, B Sza, Physical Review B, 1990 - APS
... a correlation of band offsets to transition-metal impurity levels ... a II-VI, and 0 for a group-IV semiconductor. ... The model is shown to be in fair agreement with ...
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High concentration impurity diffusion profile model - group of 2

K Suzuki, Solid State Electronics, 2000 - Elsevier
High concentration impurity diffusion profile model Kunihiko Suzuki, Fujitsu Laboratories Ltd., Atsugi Semiconductor Laboratory, 10-1 Mikumachi-Wakamaya, Atsugi ...
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Atomistic analysis of the vacancy mechanism of impurity diffusion in silicon - group of 3

S Lisi, H Ryssel, Journal of Applied Physics, 2008 - link.aip.org
... coefficients describing the coupled diffusion of impurity atoms and ... of models like the pair diffusion model [eq. M. ... Phys. [bold 48] 2169 (1977); RB Fair and JCC ...
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New model for the thickness and mismatch dependencies of threading dislocation densities in ... - group of 3

JE Ayers, Journal of Applied Physics, 2008 - link.aip.org
... densities in mismatched heteroepitaxial semiconductor layers. ... glide model are in fair agreement with ... Defects and Impurities: doping, implantation, distribution ...
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The Effect of Annealing Ambient on Dopant Diffusion in Silicon during Low-Temperature Processing

Y Kim, H Massoud, RB Fair, Journal of the Electrochemical Society, 2006 - link.aip.org
... Yuedong Kim, Hisham Z. Massoud, Richard B. Fair, ... and profile simulations using this model will be ... Doping and Impurity Implantation in germanium and silicon ...
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Shimamoto, Y.; Ugami, J.; Inoue, M.; Mizutani, M.; Hayashi, T.; Shiga, K.; Fujita, F.; Yoneda, M.; Matsuo, H.;
[VLSI Technology, 2005. Digest of Technical Papers, 2005 Symposium on](#)
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Yagyu, H.; Hayashi, S.; Tabei, O.;
[TRANSDUCERS, Solid State Sensors, Actuators and Microsystems, 12th International Conference on, 2003](#)
 Volume 1, 8-12 June 2003 Page(s):762 - 765 vol.1
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6. Modeling of anionic transient enhanced diffusion and background boron segregation in low-energy As⁺ implanted Si
 Ryangwon, K.R.; Aoki, T.; Hirose, T.; Furuta, Y.; Hayashi, S.; Shano, T.; Taniguchi, K.;
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7. Measurement of high pressure dusty SF₆ plasma generated by arc extinction in GCB
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[Plasma Science, 1998, 25th Anniversary, IEEE Conference Record - Abstracts, 1998 IEEE International on](#)
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8. Extended operation of reactor-scale fusion fuel loop under US-Japan collaboration
 Konishi, S.; Hayashi, T.; Yamashita, T.; Nakamura, H.; Naruse, Y.; Okuno, K.; Sternman, R.H.;
 Wilms, R.S.; Barnes, J.W.; Bardt, J.R.; Anderson, J.L.;
[Fusion Engineering, 1993, 15th IEEE/NPSS Symposium on](#)
 Volume 1, 11-15 Oct. 1993 Page(s):204 - 207 vol.1
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- The Electronic Properties of Transition Metal. - Jones, Resende. (Correct)
 [1] To appear in Identification of Defects in Semiconductors, edited by M. Stavola and Semiconductors and the gap manifold of states due to the impurity. Passive defects are identified. Key words: newton.ex.ac.uk/research/semiconductors/theory/people/resende/papers/EMRS/imh_pdf.pdf
- Comparisons of Nonlinear Toroidal Turbulence. - Dorland. (Correct)
 stability studies confirm the importance of impurity density gradients as a source of free energy (from 5 keV to 30 keV) is recovered by our model for dozens of simulated experiments. Finally, Comparisons of Nonlinear Toroidal Turbulence Simulations with Experiment W. Dorland, M. W3.pppl.gov/~mbeer/ris/teea_dorland.ps
- Integrating Feature Construction with Multiple Classifiers. - Vialta, Rendell (Correct)
 It is commonly a single feature, selected via some impurity measure, e.g. entropy, gini, an important advantage of symbolic learning models over other inductive models (e.g. over a www.research.ibm.com/people/v/vialta/papers/csm97.ps
- NREL/JCP-450-22928. UC Category: 1250. - Fused-Salt Electrodeposition Of. (Correct)
 films were obtained with relatively low impurity levels, demonstrating the self-purification www.nrel.gov/nrcvp/pdfs/ieee20pa.pdf
- The Holstein model in infinite dimensions - Freericks, Jarrell, Scalapino (1993) (Correct)
 system is mapped onto a self consistent (local) impurity problem in the limit of infinite spatial NSF-ITP-93-13 The Holstein model in infinite dimensions J. K. Freericks M. (Received November, 1994) ABSTRACT: Monte Carlo simulations are performed to examine superconductivity and magus.physics.georgetown.edu/papers/freericks/holstein_long.ps
- Intrinsic and Extrinsic Vortex Nucleation Mechanisms in the... - Kusmartsev Nordita (Correct)
 may be a surface aspin on smooth walls or impurity atoms like 3 He impurities in 4 He. For the situation occurs in the Williams-Shenoy(VS) 5J model of the -phase transition where the role of V-A noreg1.nordita.dk/Adm/Activities/pre96/96023a.ps.gz
- Theory of Gold-Hydrogen Complexes on Silicon - Resende, Goss, Briddon, Oberga... (Correct)
 silicon is one of the most studied defects in semiconductors. This is mainly due to its technological dark current spikes in CCDs. Gold as an isolated impurity in silicon is one of the most studied defects in the periodic table is based on the "vacancy model". [1] This maintains that their electronic newton.ex.ac.uk/research/theory/people/resende/papers/gold.ps
- Robust Linear Discriminant Trees - John (Correct) (5 citations)
 have the range 10 1g. 1 A splitting criterion (impurity function) over binary splits, mapping two with disproportionately high effect on the fitted model, are often removed from training data in order to www.vuse.vanderbilt.edu/~dfisher/ai-stat-book/book-36.ps
- On the sine-Gordon-Thirring equivalence in the presence of a... - Sheng, Gao (1995) (Correct)
 scattering of electrons off a magnetic spin impurity. Such an impurity problem, in which one paper, the relationship between the sine-Gordon model with an integrable boundary condition and the preprints.cern.ch/archive/electronic/hep-th/9512/9512011.ps.gz
- Neutrino Trapping in a Supernova and Ion Screening - Horowitz Institut (Correct)
 [5,6] and ion [6] screening. Imagine a single impurity ion in a dense plasma. Extra electrons will be other forms of matter [1] Therefore, supernova models may depend on the details of neutrino and ions is calculated from Monte Carlo simulations and parameterized with a least squares fit. preprints.cern.ch/archive/electronic/astro-ph/9603/9603138.ps.gz
- Laboratoire de Physique des Semiconducteurs. De parlement de... - Received May In (Correct)
 is a defect associated with an isolated donor impurity (for the description of its properties see [1]

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the variation of E and B versus x is obtained in a model where the DX level is a donor state associated www.wiley-vch.de/contents/jc_2232/1/209/363_a.pdf

Spherical Wavelets: Efficiently Representing Functions on... - Schröder, Sweldens (1995) (Correct) (52 citations)
 computations [16, 29] curve and surface modeling [17] and animation [18] among others. Given the such as topography and remote sensing imagery, simulation and modeling of bidirectional reflection After a section on implementation, we report on simulations and conclude with a discussion and suggestions achille.research.bell-labs.com/cn/ms/who/whim/papers/sphere.ps.gz

Performance of ATM Switch Fabrics Using Cross-Point Buffers - Zhou, Aliquazzaman (1995) (Correct)
 atq@eng.monash.edu.au Abstract A new analytical model of the finite cross-point buffered multistage ATM The results from the model were validated with simulation results. It has been shown that the model of the model are validated by comparison with simulation results. We also compare the performance of the www.engr.udelton.edu/faculty/matiqzz/papers/bin-apccc95-cam.ps

Incremental Process Support for Code Reengineering: An... - Kaiser, Heinenan... (1996) (Correct)
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Detecting Unsafe Error Recovery Schedules - Lutz, Wong (1996) (Correct) (2 citations)
 Abstract This paper presents a mechanism for modeling timing, precedence, and data-consistency and employ more concurrent processors, software simulation becomes more costly and time-consuming to checker as an embeddable module in other simulation or executable-specification tools. The www.cs.lasstate.edu/~lutz/publications/stse92.ps

Modeling Networks with VLSI (linear) Integrate-and-Fire Neurons - Mattia (Correct)
 Modeling Networks with VLSI (linear) Integrate-and-Fire 0.07 0.08 0.09 0.1 V (0 0 A) [s] Fig. 1. Simulation of depolarization dynamics at positive (A) and of this paper have been tested by extensive simulations [7] and will be published in a future work. iuplifer.roma1.infn.it/STORAGE/linicam.ps

Flexible Seasonal Long Memory and Economic Time Series - Marqus Ooms (1995) (Correct) (3 citations)
 of a flexible seasonal long memory time series model based on fractional differencing. This type of www.eur.nl/few/eb/papers/.pub/oomsart1.ps

Multiprocessor Resource Estimation Using a Stochastic... - Andrews Thornton (1996) (Correct)
 Resource Estimation Using a Stochastic Modeling Approach D. L. Andrews, M. A. Thornton, J. D. parallelism curve to that predicted by the simulation. When the maximum work criteria is used, model was developed and run using the SIMSCRIPT simulation language [4] The model consisted of a set of hp.engr.uark.edu/ftp/user/matt1/pubs/spdp96.ps

Architectural Adaptation for Application-Specific... - Zhang, Dasdan... (1997) (Correct) (2 citations)
 adaptation is in the key trends in the semiconductor technology. In particular, the difference in these technology trends and advances in circuit modeling using hardware description languages (HDLs) such Structures We perform cycle-based system-level simulation using a program-driven simulator based on MINT www.csag.ucsd.edu/papers/csag/external/ccd97.ps

RMM's Solution Concept and the Equilibrium Point Solution - Vidal, Durfee (1994) (Correct) (1 citation)
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